

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

PESD3V3L1BA,115-MS

Product specification

Features

- 350Watts peak pulse power (tp = 8/20μs)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 ±30kV contact ±30kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 20A (8/20μs)

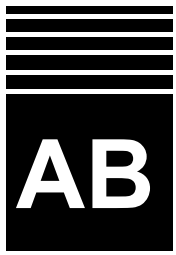
Mechanical Data

- SOD-323 package
- Molding compound flammability rating: UL94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Applications

- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Pagers Peripherals

Reference News

SOD-323	GRAPHIC SYMBOL	MARKING
		

Absolute Maximum Rating

Parameters	Symbol	Value	Unit
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{PP}	350	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I_{pp}	20	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	30 30	kV
Lead Soldering Temperature	T_L	260(10seconds)	$^{\circ}C$
Junction Temperature	T_J	-55 to + 150	$^{\circ}C$
Storage Temperature	T_{stg}	-55 to + 150	$^{\circ}C$

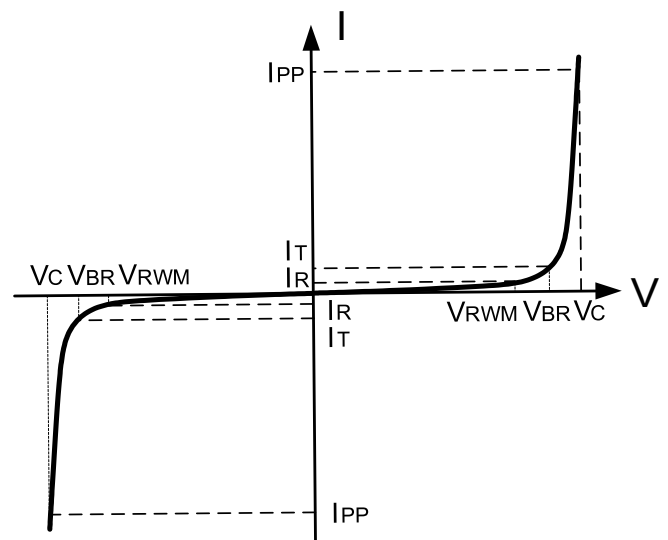
Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				3.3	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1mA$	4.2			V
Reverse Leakage Current	I_R	$V_{RWM} = 3.3V, T = 25^{\circ}C$			0.5	μA
Clamping Voltage	V_C	$I_{PP} = 20A, t_p = 8/20\mu s$			26	V
Junction Capacitance	C_j	$V_R = 0V, f = 1MHz$		65		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

Note: 8/20 μs pulse waveform.



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

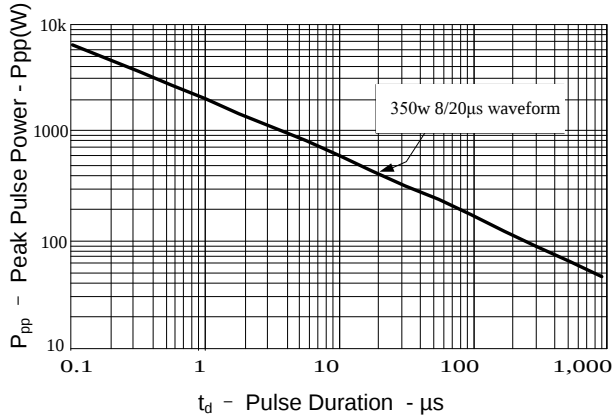


Figure 2: Power Derating Curve

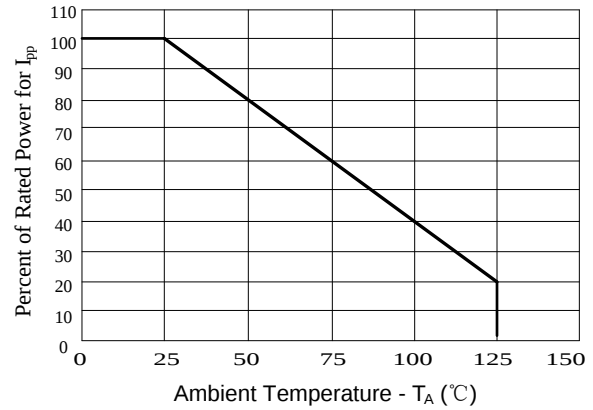


Figure3: Pulse Waveform

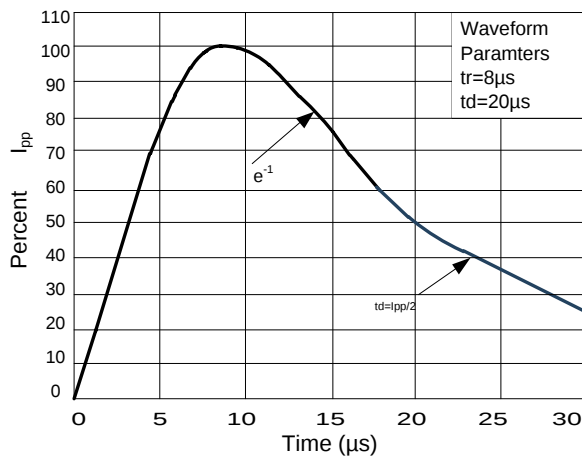
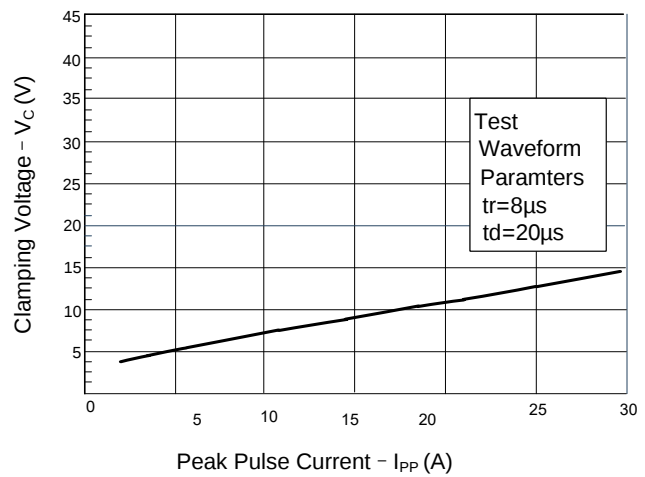
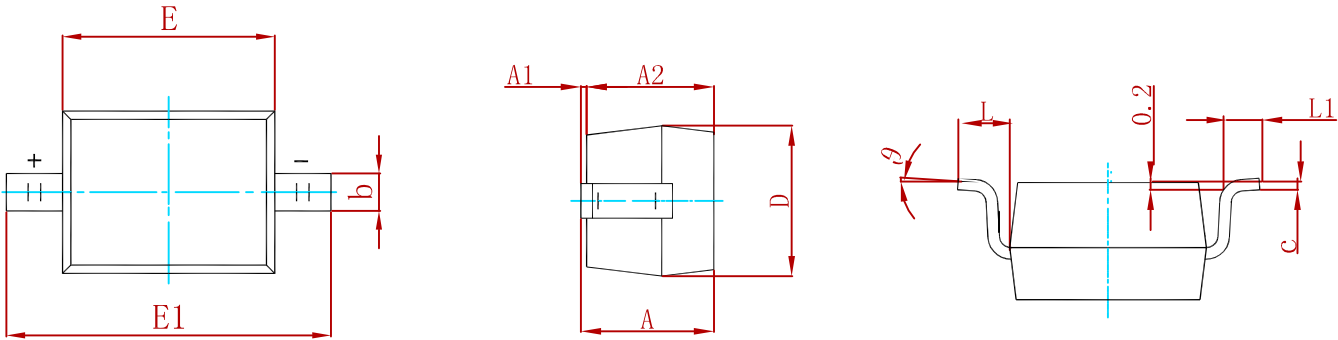


Figure 4: Clamping Voltage vs. Ipp

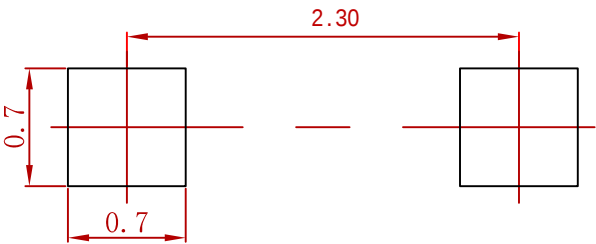


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.050		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.950	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.450	0.010	0.016
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
PESD3V3L1BA,115-MS	SOD-323	3000

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